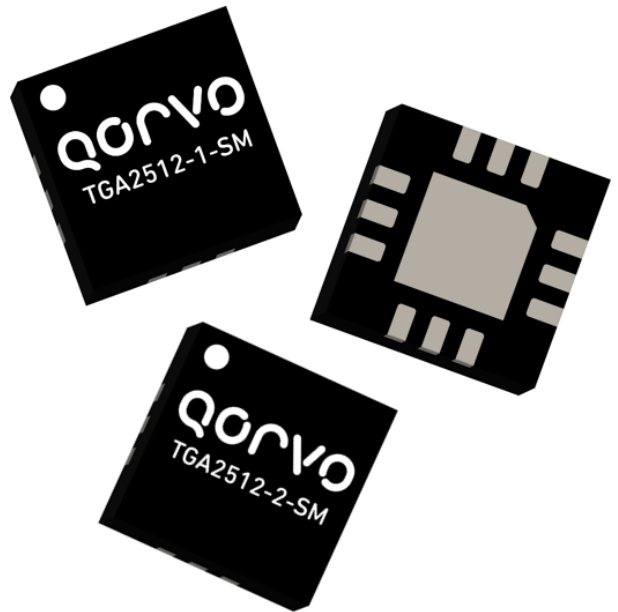


Product Description

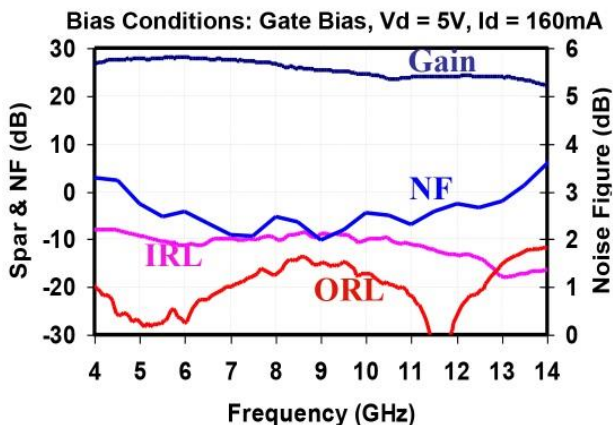
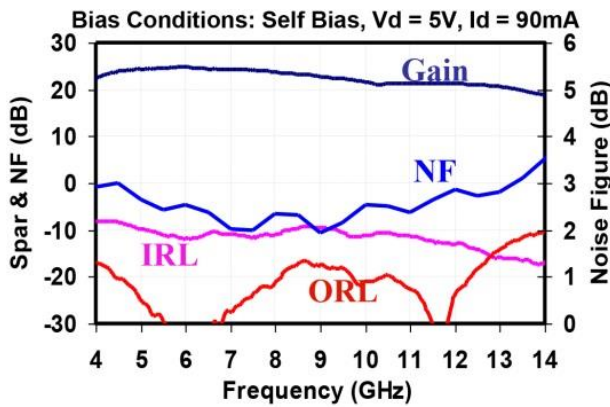
The Qorvo TGA2512-SM is a packaged X-band balanced LNA with AGC amplifier for EW, ECM, and RADAR receiver or driver amplifier applications. Based on Qorvo’s GaAs 3MI pHEMT process, the TGA2512-SM provides excellent noise performance with typical midband NF of 2.3 dB, with a high gain of 25 dB from 4-14.2 GHz

The TGA2512-SM is designed for maximum ease of use. TGA2512-SM can handle up to 21 dBm input power reliably, while the build-in gain control provides 15 dB of typical gain control range. The part can be used in self-biased mode, with a single +5 V supply connection, or in gate biased mode, allowing the user to control the current for a particular application.

In self-biased mode the TGA2512-SM achieves 6 dBm typical P1 dB, while in gate-biased mode the typical P1 dB is over 13 dBm.



Measured Data



Key Features

- Frequency Range: 4–14.2 GHz
- 2.3 dB Nominal Noise Figure
- 25 dB Nominal Gain
- 15 dB AGC Range
- 13 dBm Nominal P1dB
- 24 dBm Nominal OIP3
- Bias: 5 V, 160 mA Gate Bias, 5 V, 90 mA Self Bias
- Package Dimensions: 4.0 x 4.0 x 0.9 mm

Applications

- X-Band Radar
- EW, ECM
- Point-to-Point Radio

Ordering Information

Part No.	Package Style
TGA2512-1-SM	QFN 4 x 4 Surface Mount – Self Bias
TGA2512-2-SM	QFN 4 x 4 Surface Mount – Gate Bias
1059405	TGA2512-1-SM Evaluation Board
TGA2512-2-SMEVB1	TGA2512-2-SM Evaluation Board

MAXIMUM RATINGS 1/

Symbol	Parameter	Value	Notes
V _d	Drain Voltage	Gate Bias: $[4 + (0.009)(I_d)]$ V	<u>2/</u> <u>3/</u>
		Self Bias: $[3.5 + (0.022)(I_d)]$ V	
V _g	Gate Voltage Range	-1 TO +0.5 V	
I _d	Drain Current (gate biased)	240 mA	<u>2/</u>
I _g	Gate Current	7.04 mA	
P _{IN}	Input Continuous Wave Power	21 dBm	
P _D	Power Dissipation	1.56 W	<u>2/</u> <u>4/</u>
T _{CH}	Operating Channel Temperature	200 °C	<u>5/</u>
	Mounting Temperature (30 Seconds)	260 °C	
T _{STG}	Storage Temperature	-65 to 150 °C	

1/ These ratings represent the maximum operable values for this device.

2/ Combinations of supply voltage, supply current, input power, and output power shall not exceed P_D.

3/ Unit for I_d is mA.

4/ When operated at this bias condition with a base plate temperature of 85 °C, the median life is 9.3E4 hours.

5/ Junction operating temperature will directly affect the device median time to failure (T_m). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.

Electrical Characteristics

T_A = 25 °C, Nominal

Parameter	Self Bias TGA2512-1-SM	Gate Bias TGA2512-2-SM	Units
Frequency Range	4–14.2	4–14.2	GHz
Drain Voltage, V _D	5.0	5.0	V
Drain Current, I _D	160	160	mA
Gate Voltage, V _G	-	-0.1	V
Small Signal Gain, S ₂₁	22	25	dB
Input Return Loss, S ₁₁	-10	-10	dB
Output Return Loss, S ₂₂	-20	-20	dB
Noise Figure, NF	2.3	2.3	dB
Output Power @ 1 dB Gain Compression, P ₁ dB	6	13	dBm
OIP ₃	16	24	dBm
Temperature Gain Coefficient	-0.02	-0.02	dB/°C

Note: Table II Lists the RF Characteristics of typical devices as determined by fixture measurements.

TGA2512-2-SM Electrical Characteristics

V_D = 5 V, I_D = 160 mA, V_{CTRL} = 0 V, T_A = 25 °C, Nominal

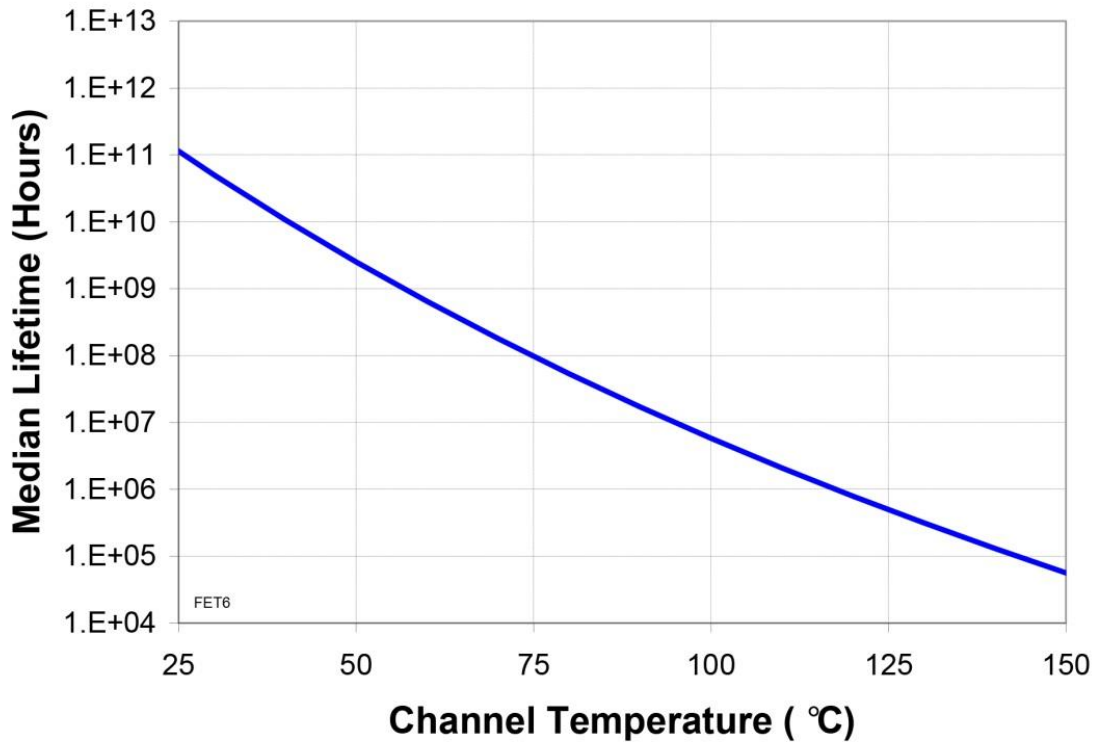
Parameter	Min	Typ	Max	Units
Frequency Range	11		14.2	GHz
Drain Current, I _D		160	200	mA
Gate Voltage, V _G	-0.4	-0.1	0.2	V
Small Signal Gain, S ₂₁	19	24		dB
Input Return Loss, S ₁₁	-7	-12		dB
Output Return Loss, S ₂₂	-7	-12		dB
Noise Figure, NF		3	4.5	dB
Output Power @ 1 dB Gain Compression, P ₁ dB	10	13		dBm
OIP ₃	16	22		dBm

Thermal Information

Parameter	Test Conditions	T _{CH} (°C)	Θ _{JC} (°C/W)	T _M (HRS)
Θ _{JC} Thermal Resistance (channel to Case)	V _D = 5 V I _D = 160 mA Gate Bias P _{diss} = 0.80 W	115	37.6	1.3E+6
Θ _{JC} Thermal Resistance (channel to Case)	V _D = 5 V I _D = 90 mA Self Bias P _{DISS} = 0.45 W	97.7	28.2	7.2E+6

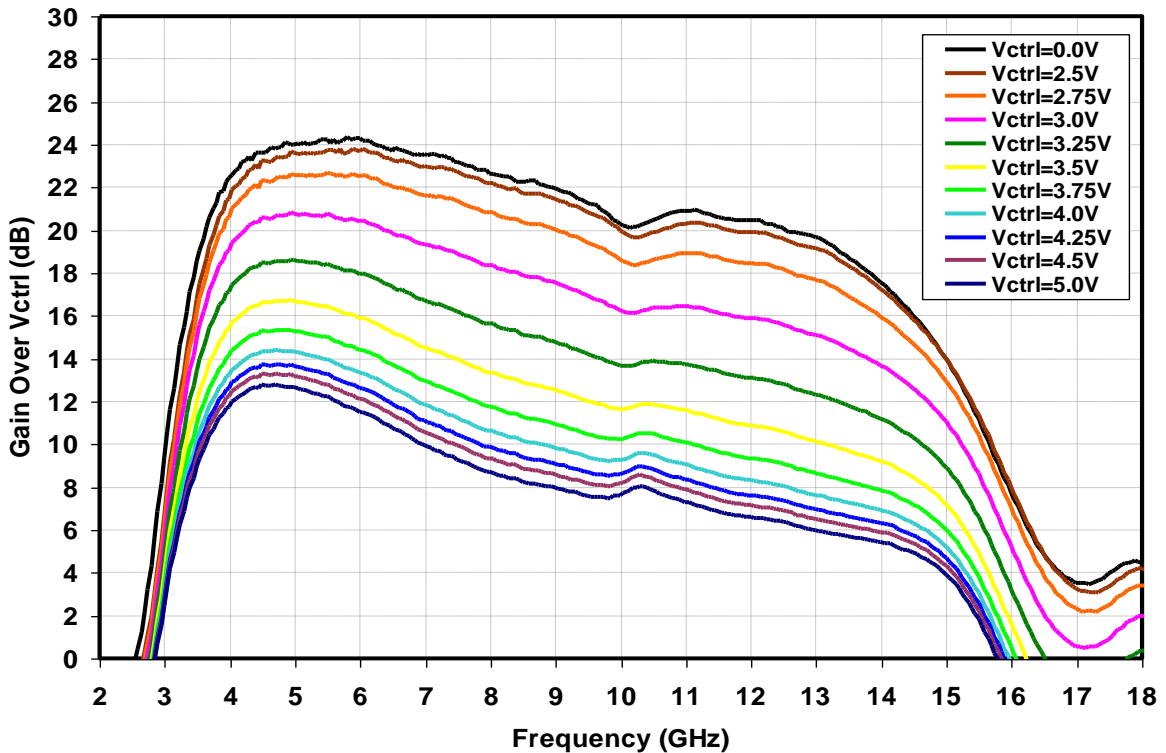
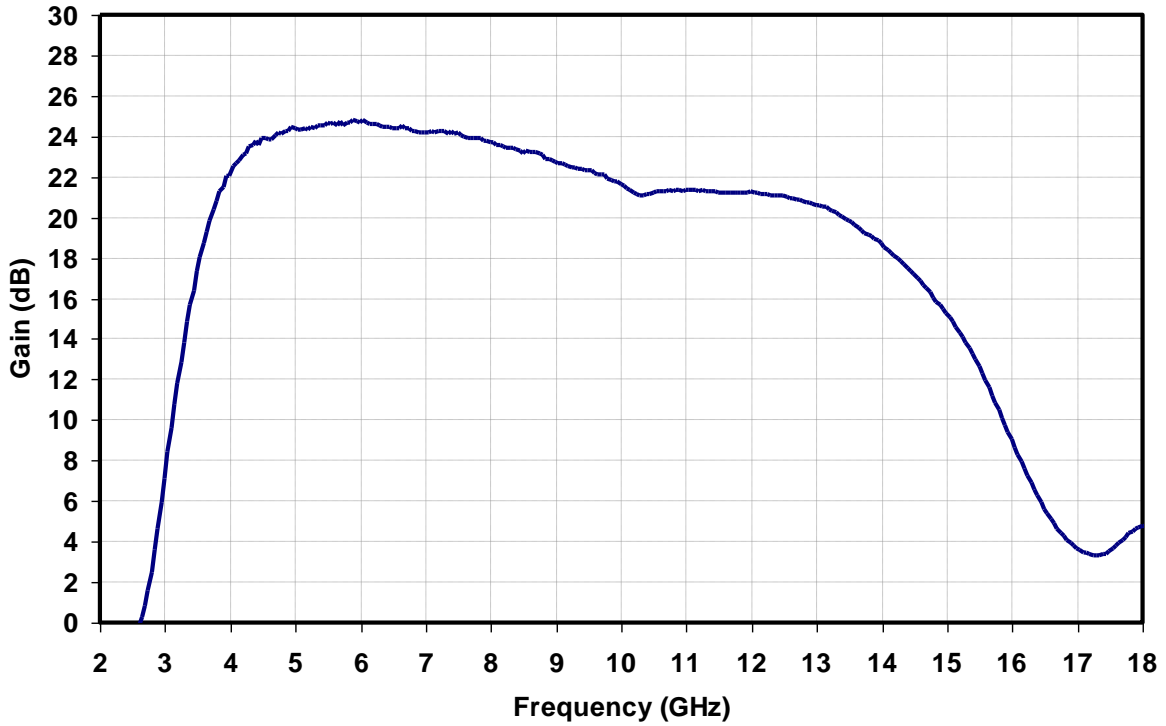
Note: Worst case condition with no RF applied. 100% of DC power is dissipated. Case temperature at 85 °C

Median Lifetime (T_m) vs. Channel Temperature



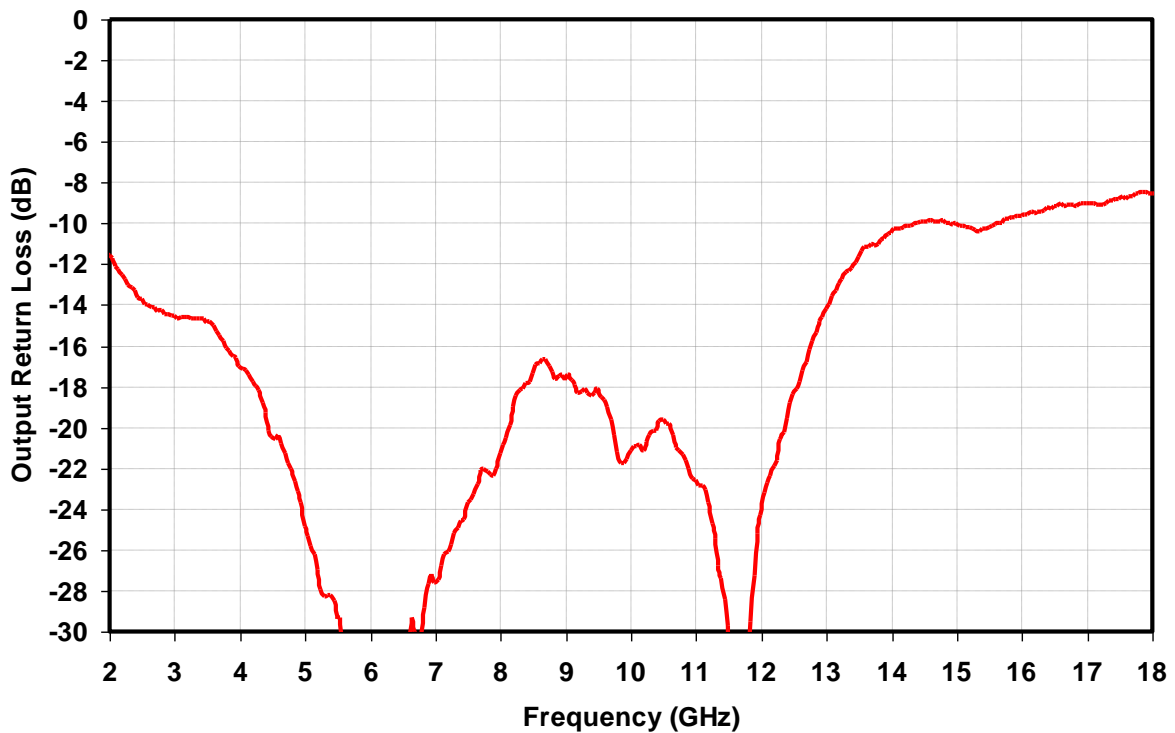
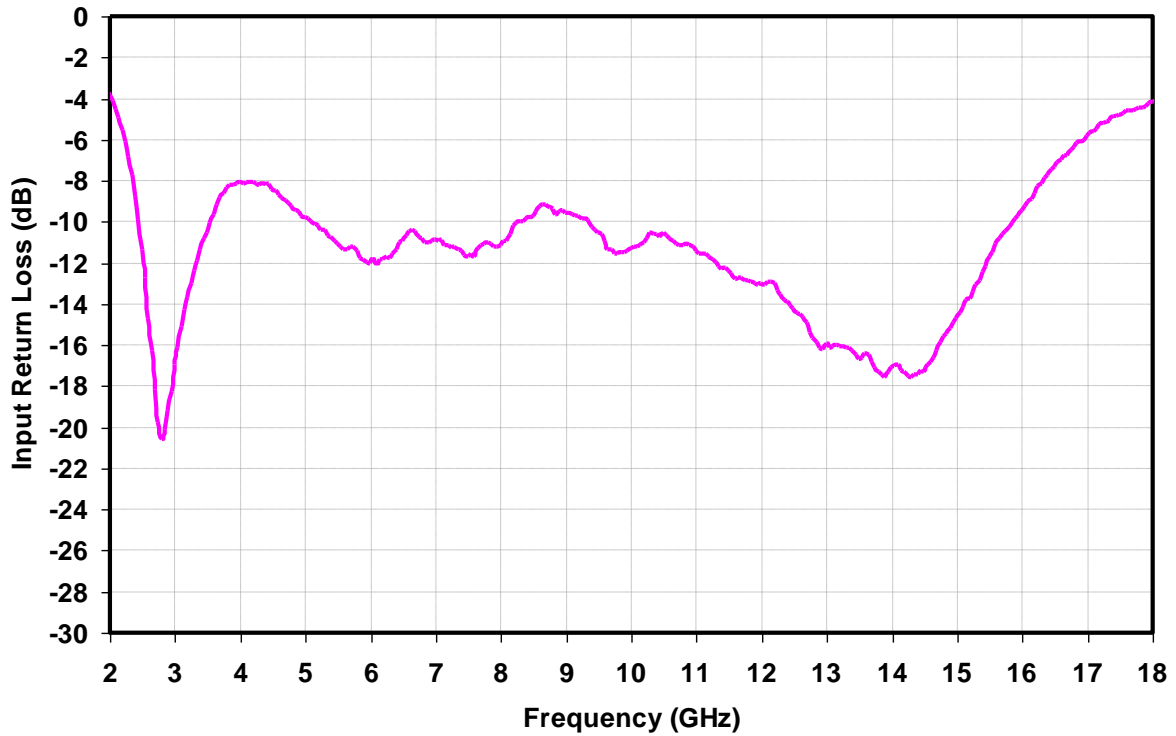
Measured Data

Bias Conditions: Self Bias, $V_D = 5\text{ V}$, $I_D = 90\text{ mA}$



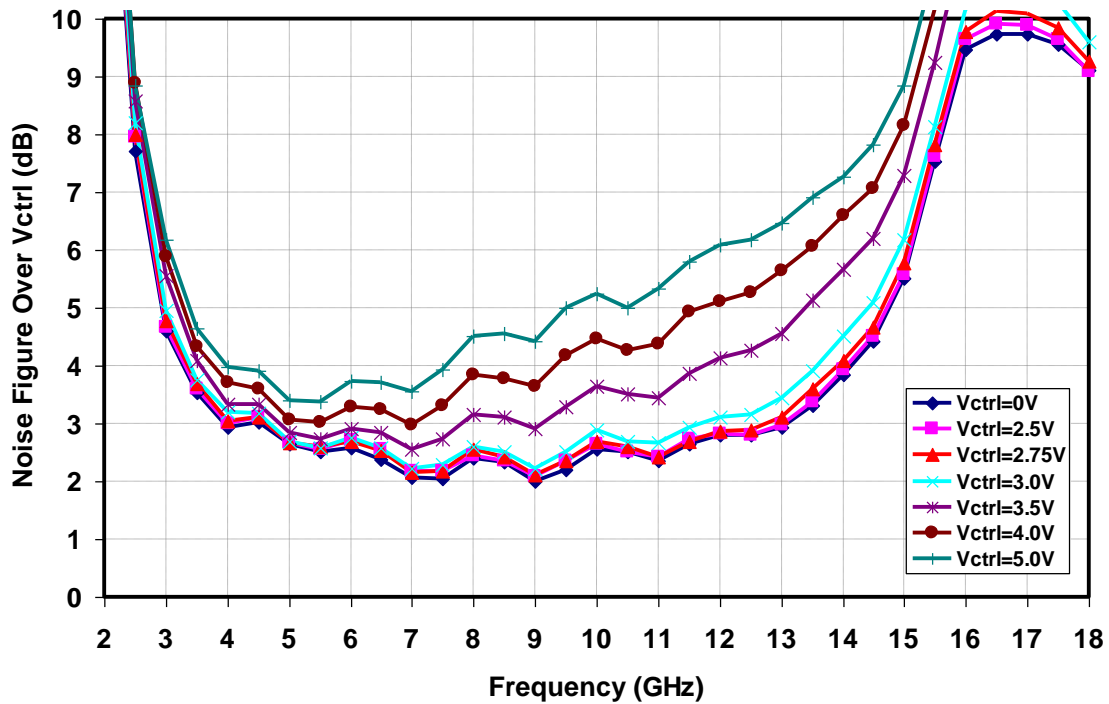
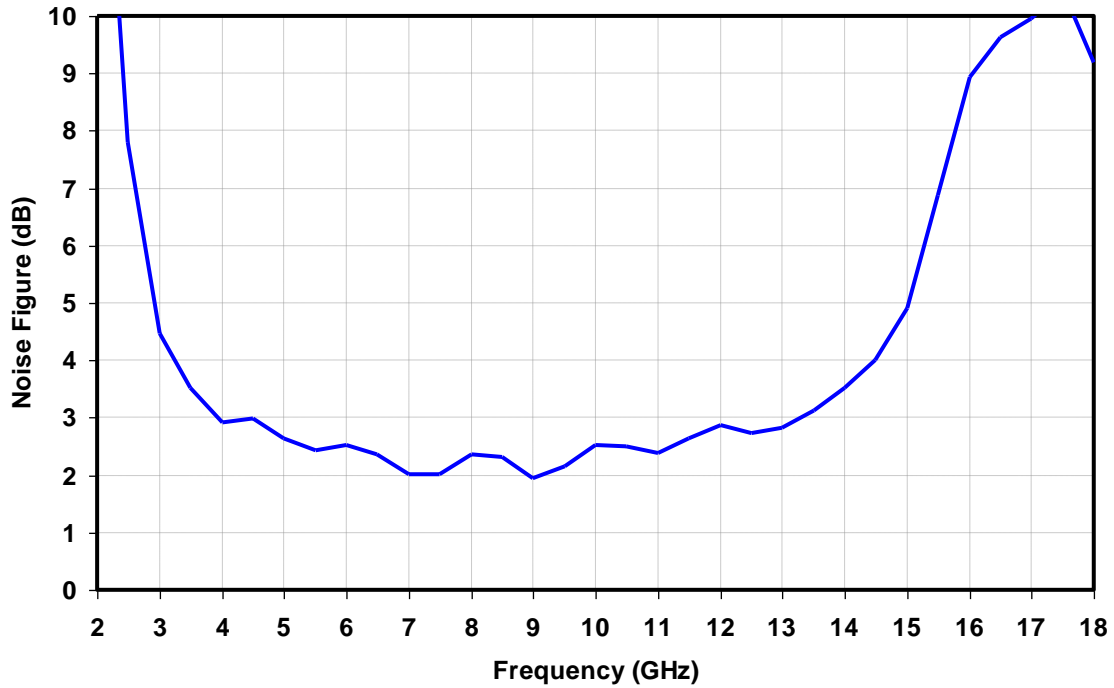
Measured Data

Bias Conditions: Self Bias, $V_D = 5\text{ V}$, $I_D = 90\text{ mA}$



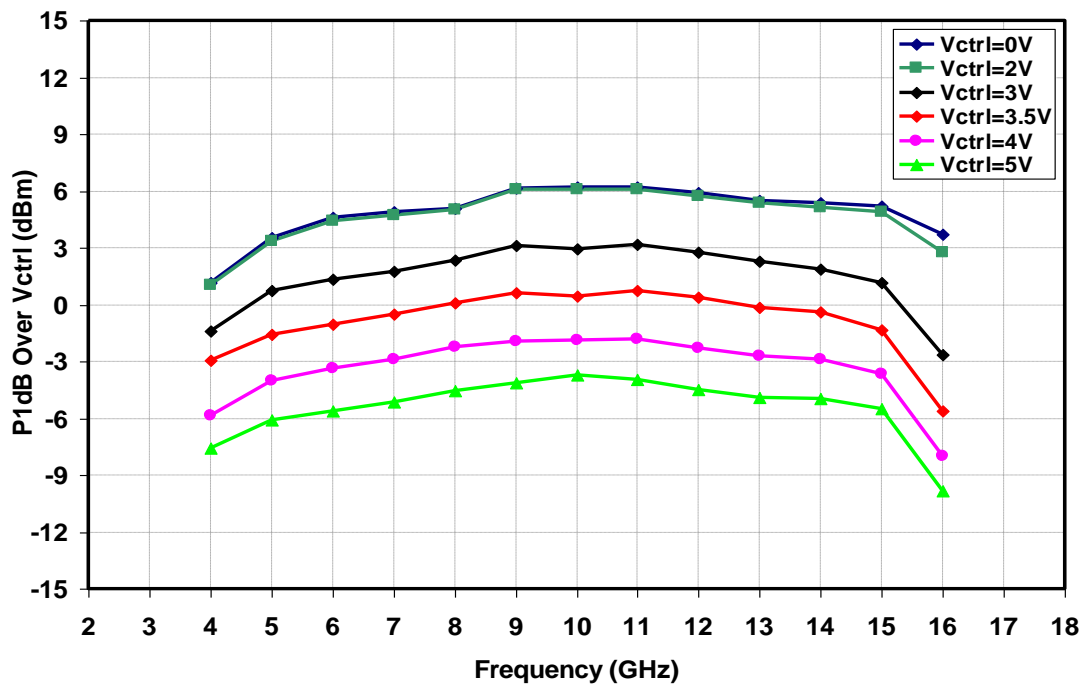
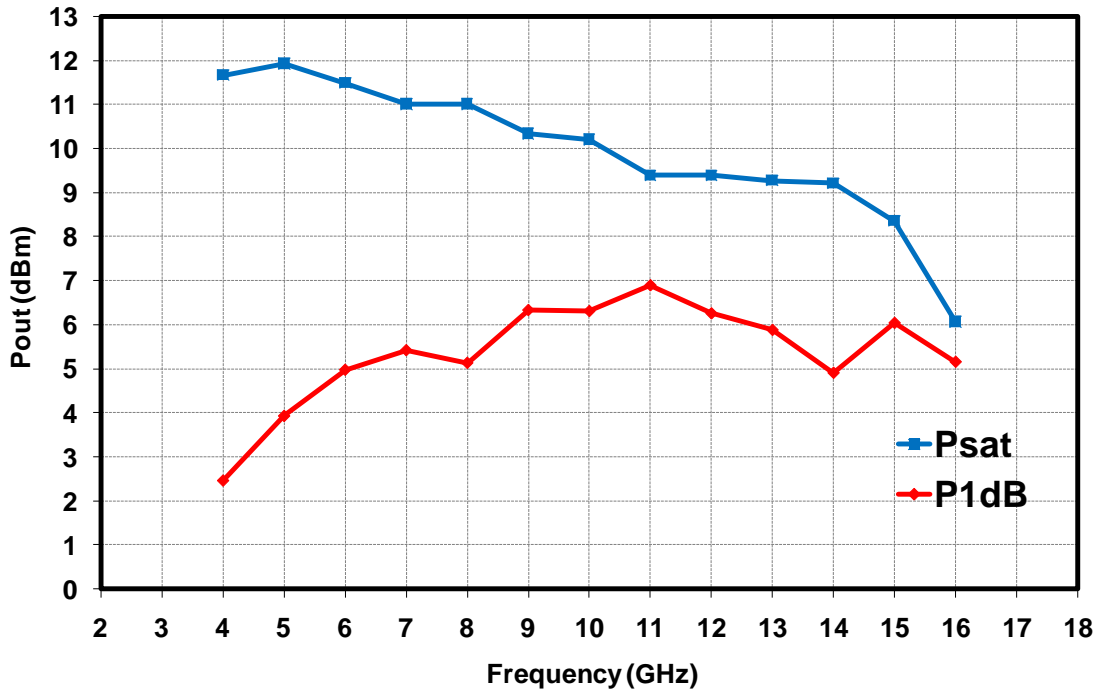
Measured Data

Bias Conditions: Self Bias, $V_D = 5\text{ V}$, $I_D = 90\text{ mA}$



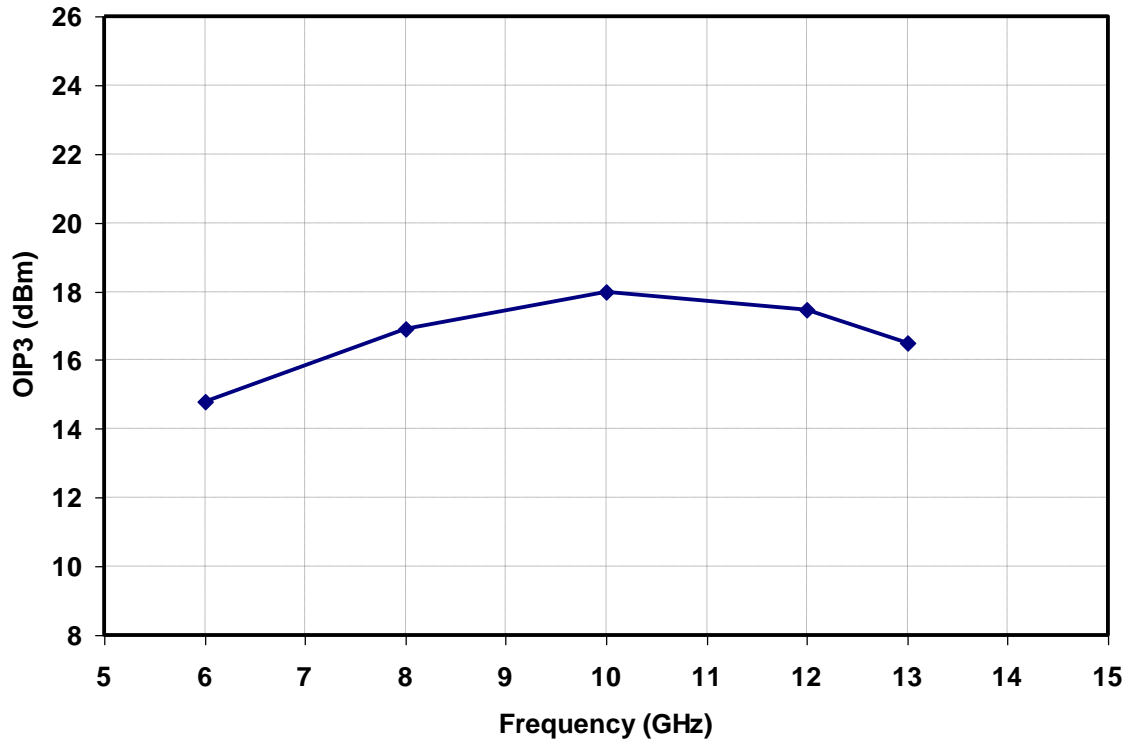
Measured Data

Bias Conditions: Self Bias, $V_D = 5\text{ V}$, $I_D = 90\text{ mA}$



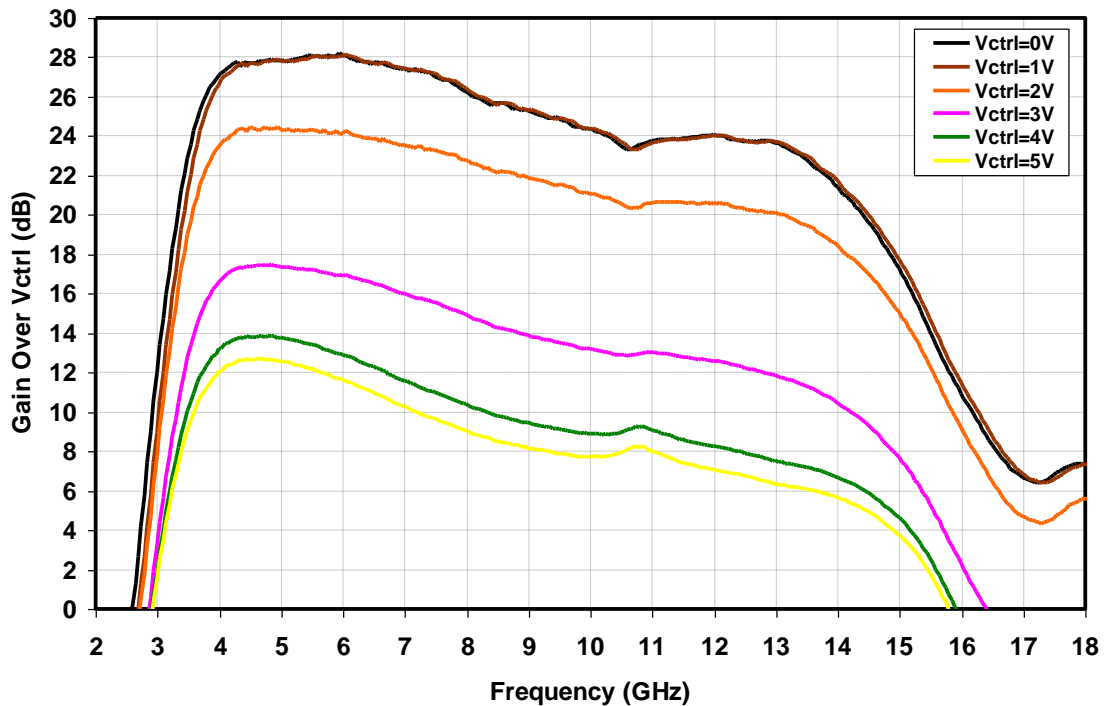
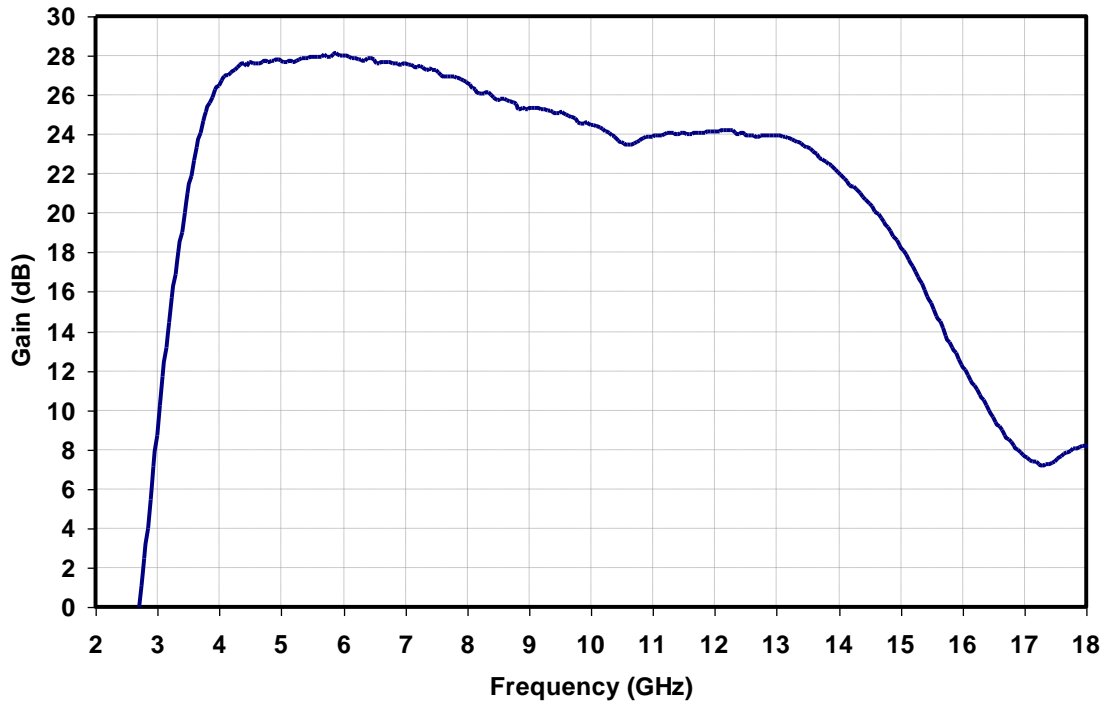
Measured Data

Bias Conditions: Self Bias, $V_D = 5\text{ V}$, $I_D = 90\text{ mA}$



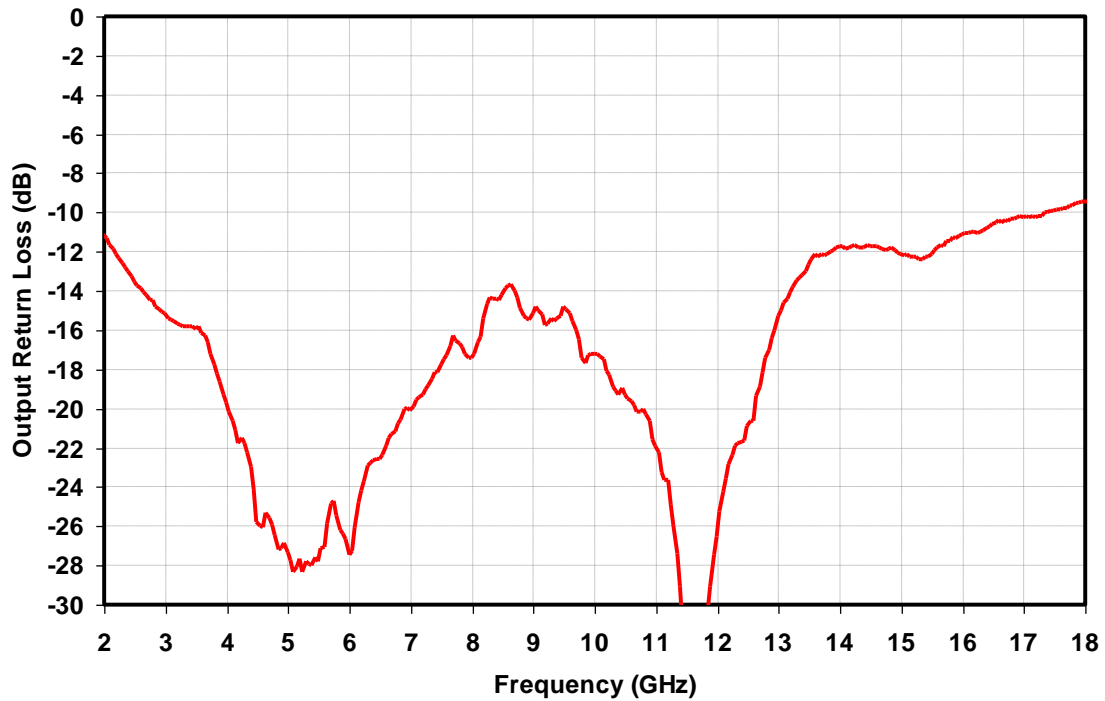
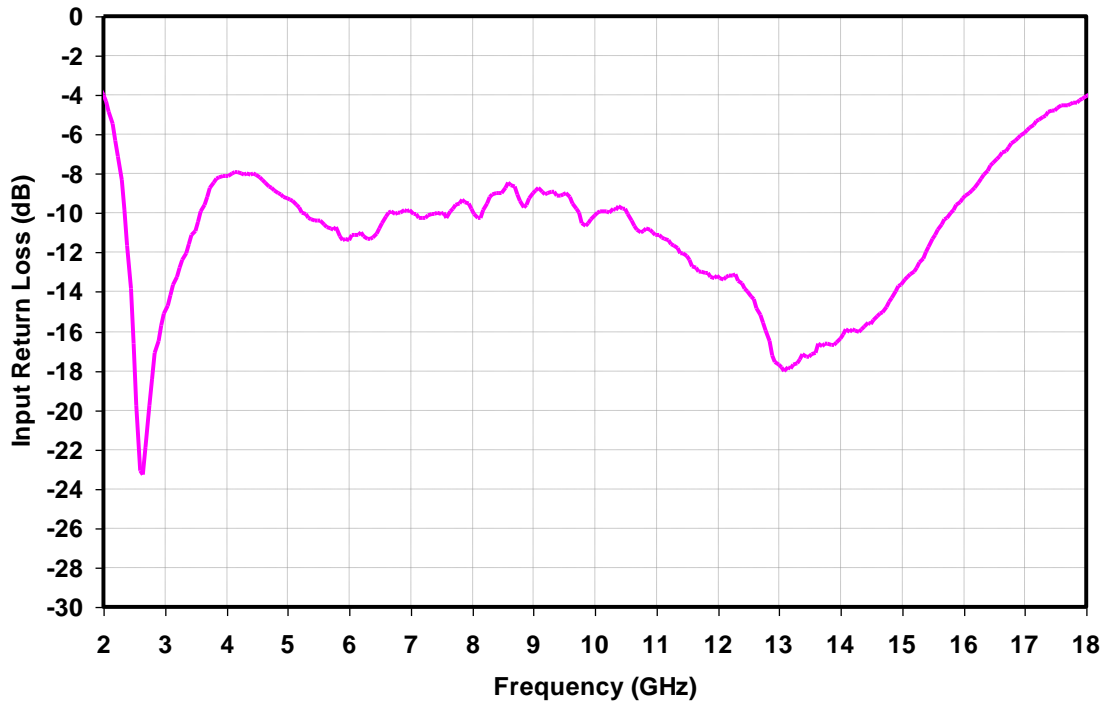
Measured Data

Bias Conditions: Gate Bias, $V_D = 5\text{ V}$, $I_D = 160\text{ mA}$



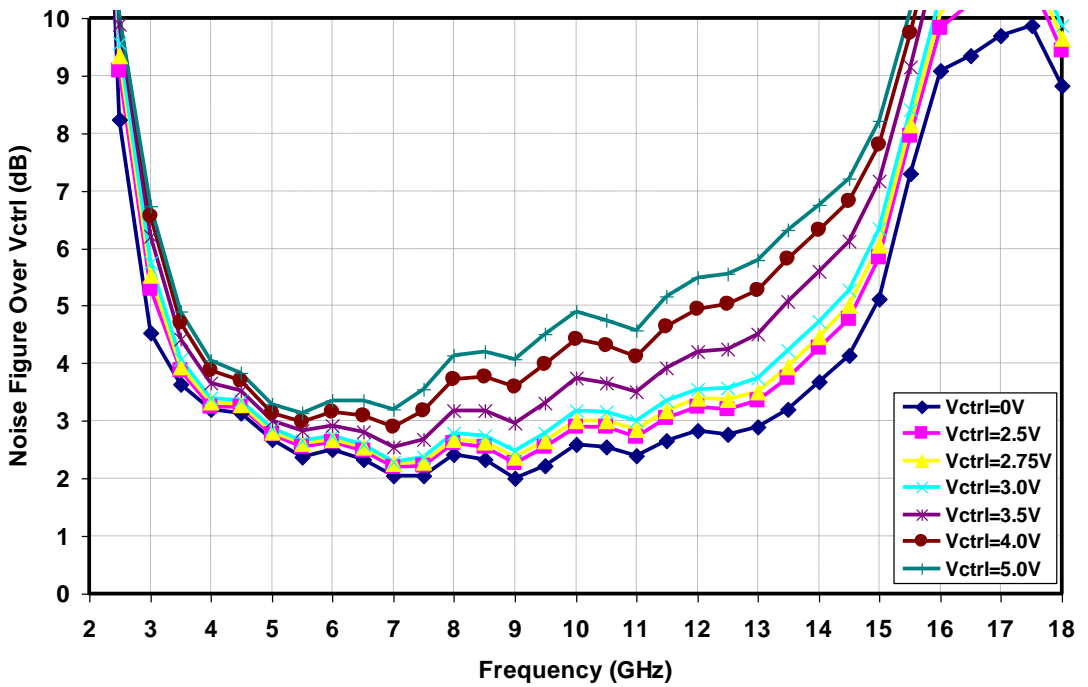
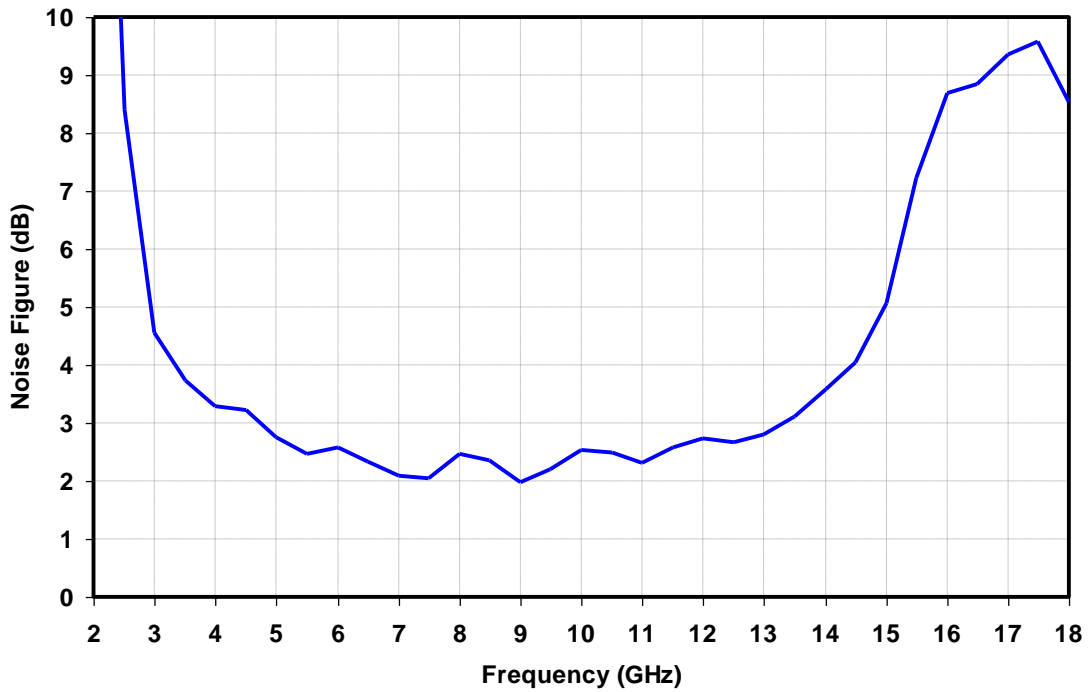
Measured Data

Bias Conditions: Gate Bias, $V_D = 5\text{ V}$, $I_D = 160\text{ mA}$



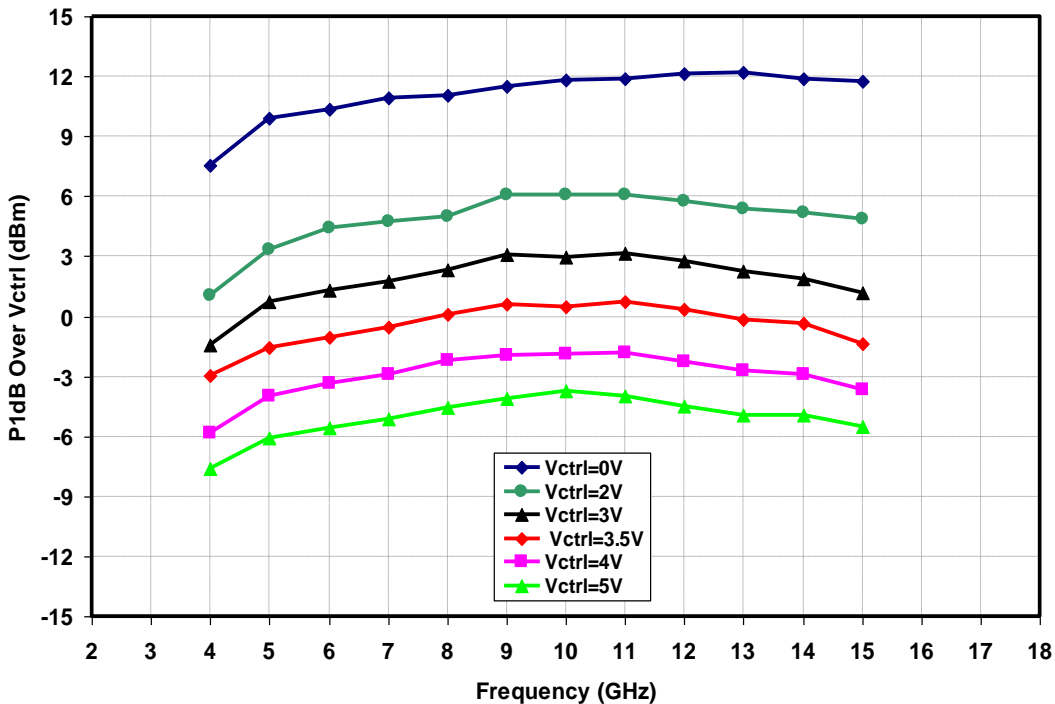
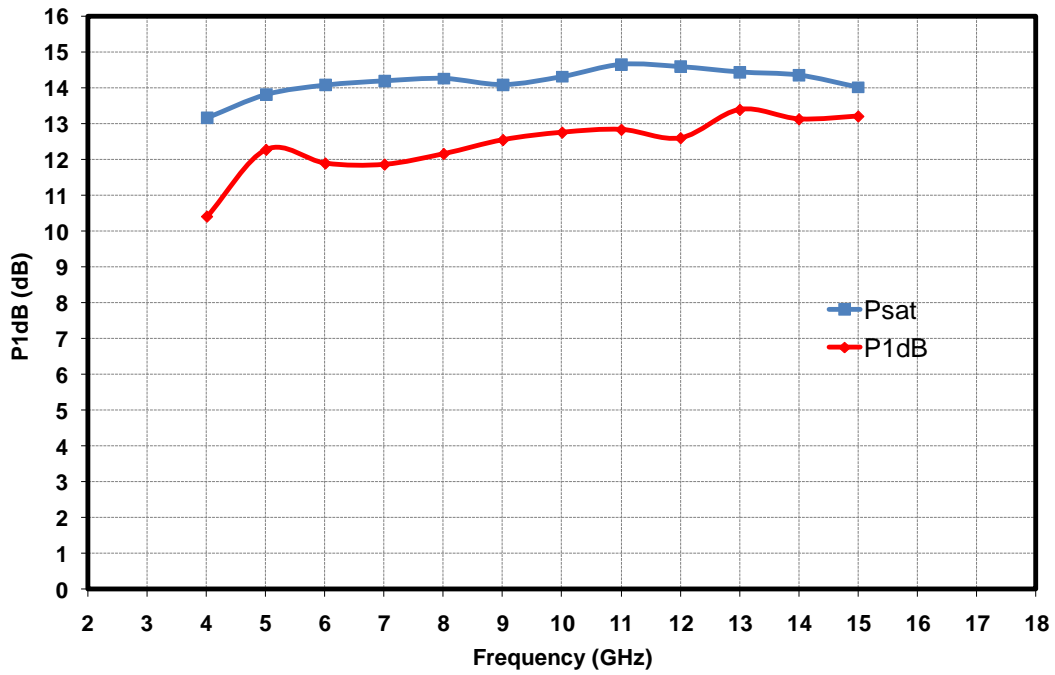
Measured Data

Bias Conditions: Gate Bias, $V_D = 5\text{ V}$, $I_D = 160\text{ mA}$



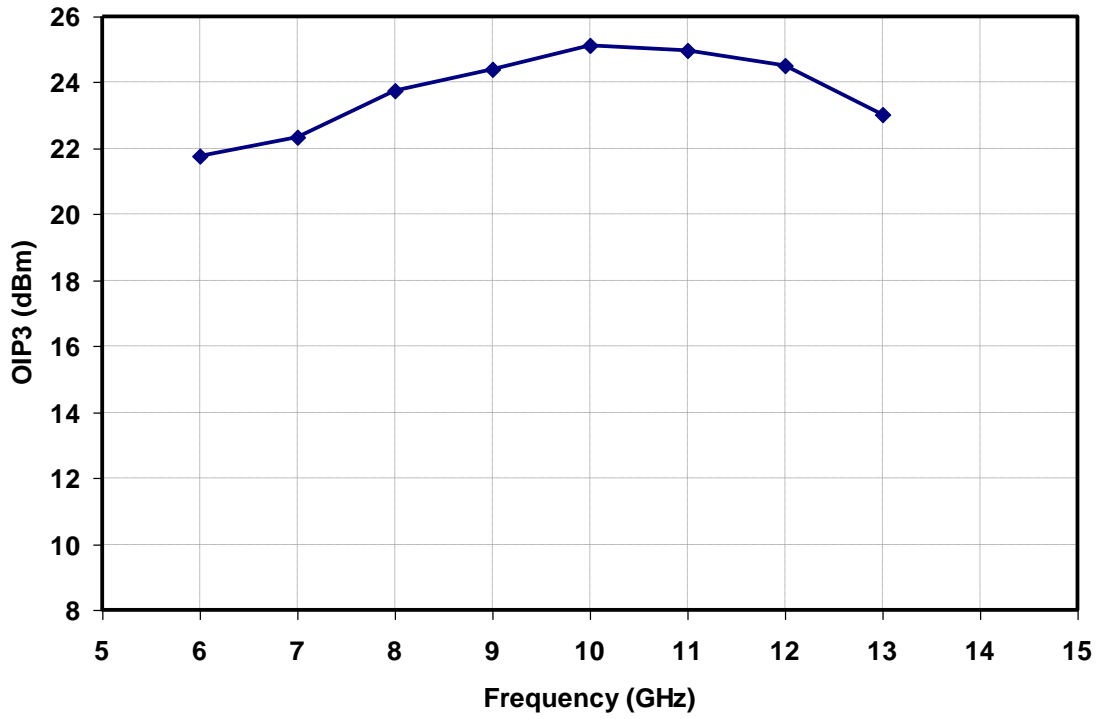
Measured Data

Bias Conditions: Gate Bias, $V_D = 5\text{ V}$, $I_D = 160\text{ mA}$

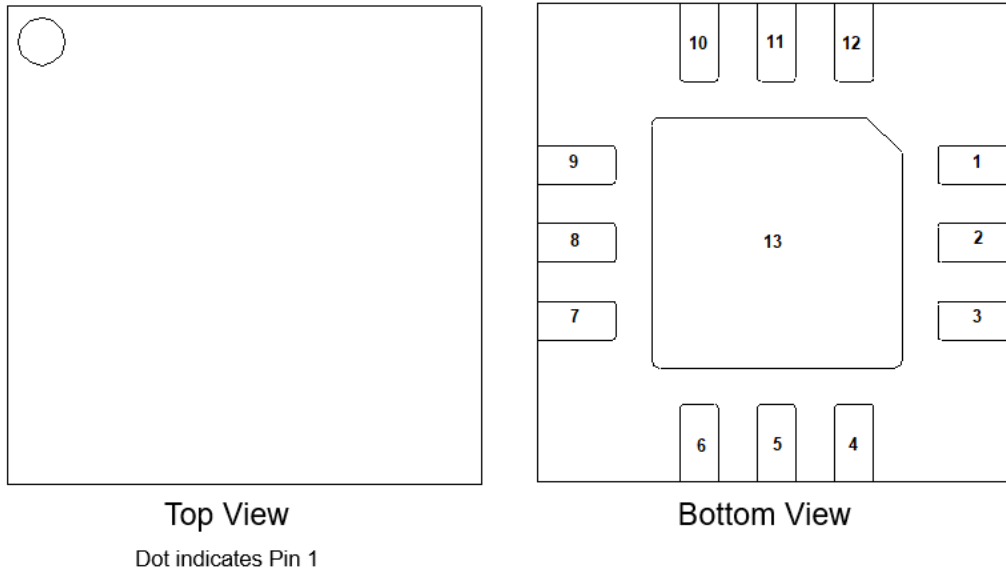


Measured Data

Bias Conditions: Gate Bias, $V_D = 5\text{ V}$, $I_D = 160\text{ mA}$



Package Pinout Diagram



Self Bias

Pin	Description
1,3, 4, 5, 6, 7, 9, 12	NC
2	RF Input
8	RF Output
10	Vd
11	Vctrl
13	GND

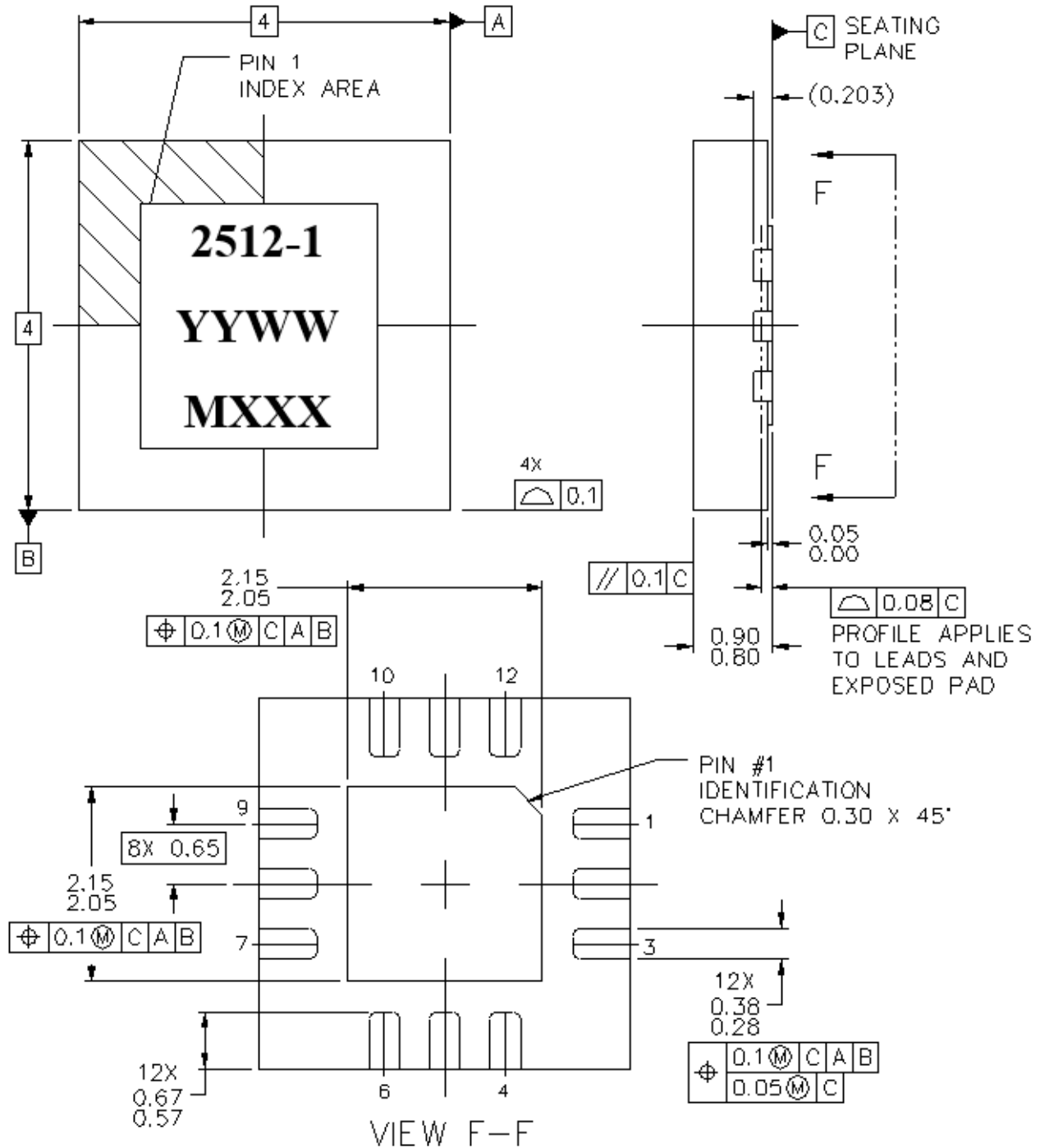
Self Bias: $V_D = 5\text{ V}$ ($I_D = \sim 90\text{ mA}$), $V_{CTRL} = 0\text{ to }+5\text{ V}$ for Gain adjustment

Gate Bias

Pin	Description
1,3, 4, 5, 6, 7, 9	NC
2	RF Input
8	RF Output
10	Vd
11	Vctrl
12	Vg
13	GND
13	Gnd

Gate Bias: $V_D = 5\text{ V}$, $V_{CTRL} = 0\text{ to }+5\text{ V}$ for Gain adjustment $V_G = \text{Range, } -0.5\text{ to }0$, typically ~ -0.1 will provide $\sim 160\text{ mA}$ of I_d .

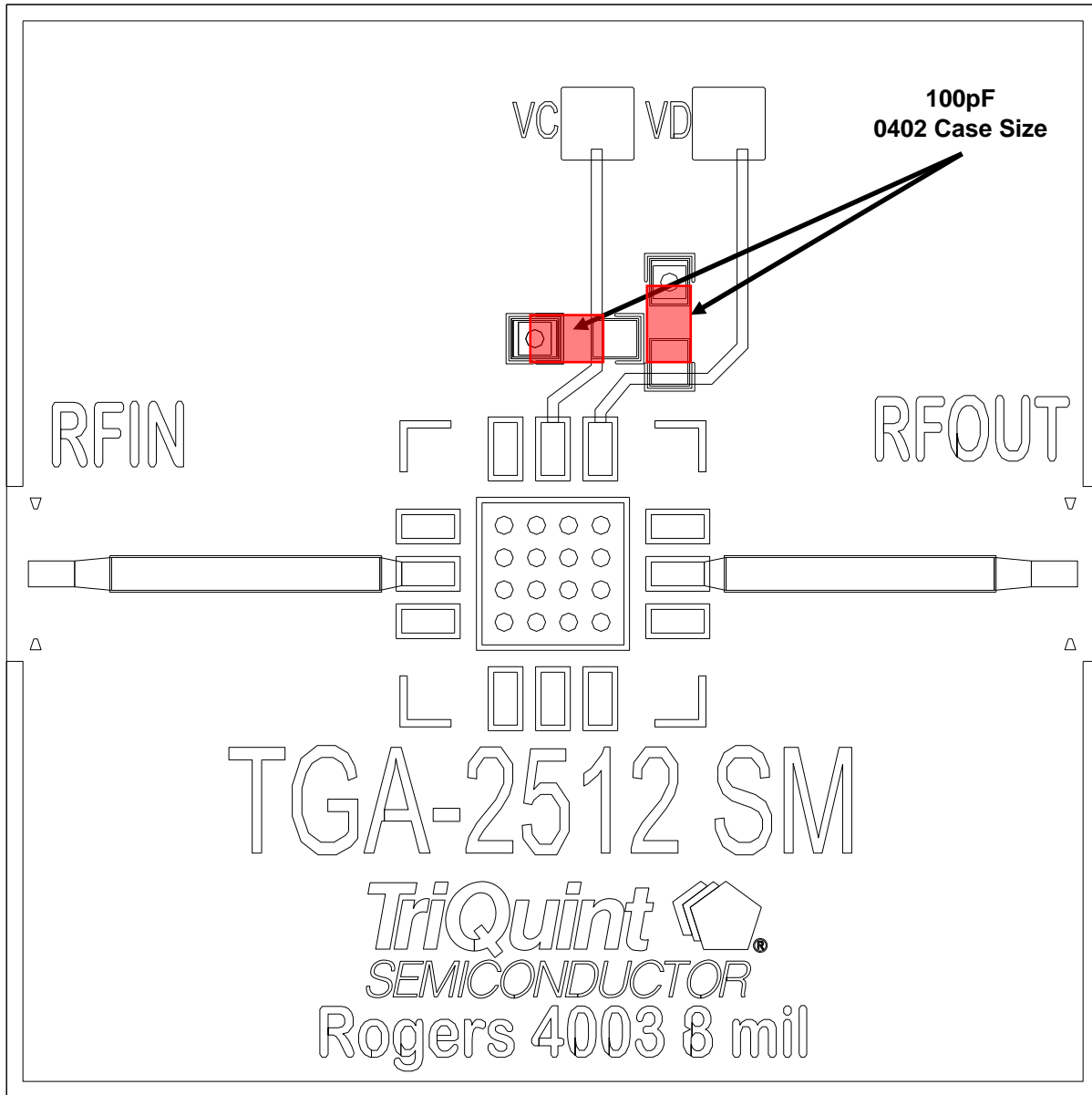
Mechanical Drawing



Dimensions in mm, package is mold encapsulated with Tin plated lead finish
 Part Marking: 2512-1/2512-2: Part Number, YY = Part Assembly Year
 WW = Part Assembly Week, MXXX = Batch ID

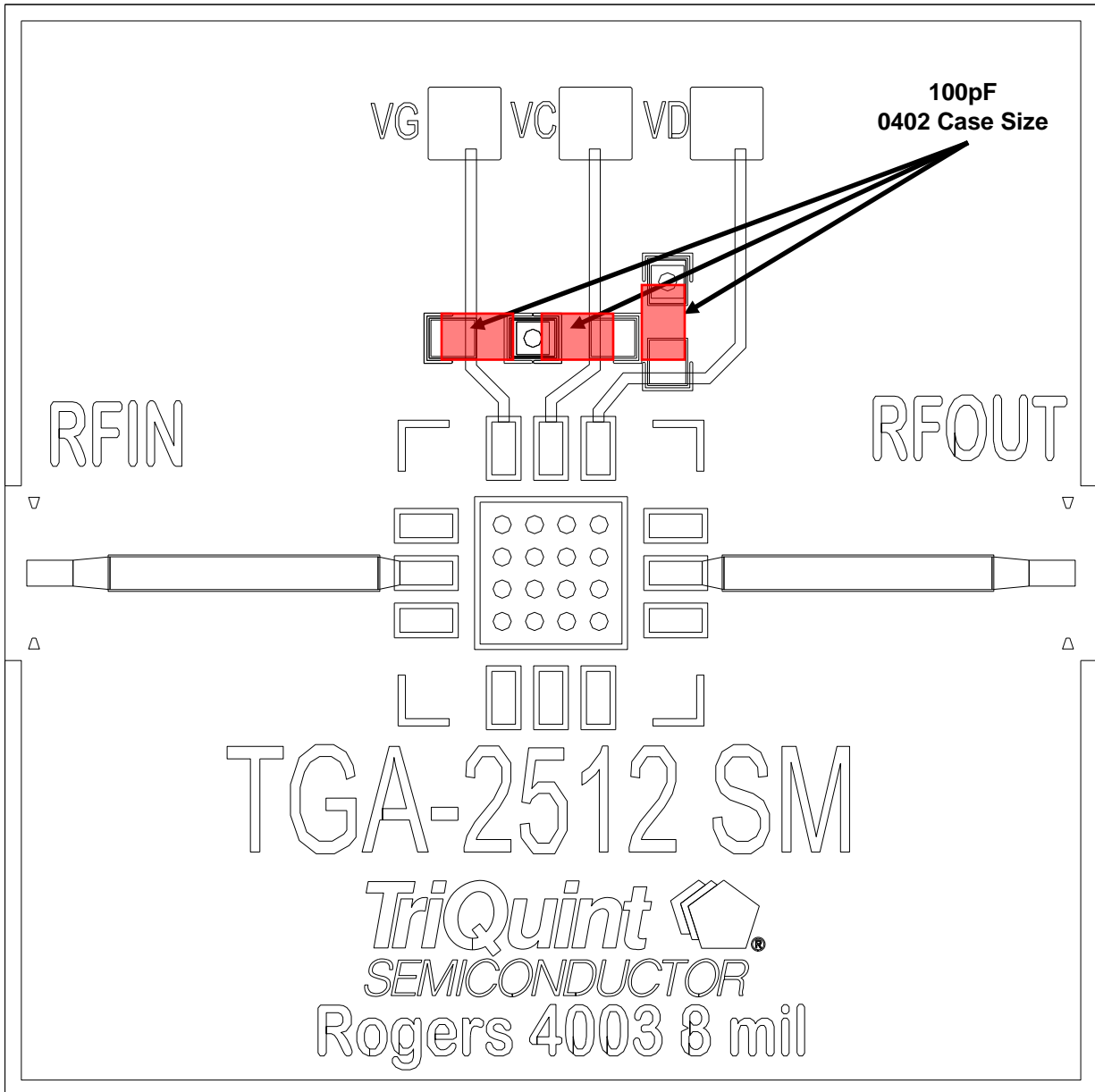
Recommended Board Layout Assembly

Self Bias



Recommended Board Layout Assembly

Gate Bias



Handling Precautions

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	TBD	ANSI/ESD/JEDEC JS-001



Caution!

ESD-Sensitive Device

Solderability

Use only AuSn (80/20) solder, and limit exposure to temperatures above 300 °C to 3 – 4 minutes, maximum.

RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C15H12Br4O2) Free
- PFOS Free
- SVHC Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: www.qorvo.com

Tel: 1-844-890-8163

Email: customer.support@qorvo.com

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